Contents

1. Introduction .............................................. 1
  1.1 Historical Remarks .................................. 1
  1.2 Surface Space-Charge and Surface States:
       Some Preliminary Remarks ......................... 13

2. Surface Space-Charge Region in Thermal Equilibrium .... 21
  2.1 Solutions of Poisson’s Equation ..................... 21
  2.2 Surface Space-Charge ................................ 25
  2.3 Shape of Surface Barriers ............................ 27
  2.4 Comparison of Space-Charge Layers
       at Semiconductor and Metal Surfaces ............... 28
  2.5 Quantum Size-Effects in Space-Charge Layers ........ 28

3. Surface States ......................................... 33
  3.1 Virtual Gap States of the Complex Band Structure .... 33
  3.2 Intrinsic Surface States: Nearly Free Electron Model .. 36
  3.3 Intrinsic Surface States: Tight-Binding Approximation ... 44
  3.4 Dangling Bonds ...................................... 47
  3.5 Adatom-Induced Surface States: Tight-Binding Approach ... 51
  3.6 Adatom-Induced Surface Dipoles: Electronegativity Concept . 53
  3.7 Adatom-Induced Surface States and Dipoles: ViGS Model ... 56

4. Occupation of Surface States and Surface Band-Bending
   in Thermal Equilibrium .................................. 59

5. Surface Space-Charge Region in Non-Equilibrium .......... 67
  5.1 Surface Photovoltage .................................. 67
  5.2 Dember Effect ....................................... 73
  5.3 Surface Transport .................................... 74
     5.3.1 Surface Excess of Carriers ..................... 74
     5.3.2 Surface Conductance ............................ 76
     5.3.3 Surface Mobility ............................... 76
     5.3.4 Field Effect of Surface Conductance ............ 78
6. Interface States .................................................. 81
   6.1 Metal–Semiconductor Contacts: Metal–Induced Gap States .. 81
   6.2 MIGS-and-Electronegativity Model
       of Metal–Semiconductor Contacts .......................... 86
   6.3 Slope Parameters of Barrier Heights in Schottky Contacts .. 91
   6.4 Defects at Metal–Semiconductor Interfaces .................... 93
   6.5 Band Lineup in Semiconductor Heterostructures:
       IFIGS-and-Electronegativity Model ............................ 96
   6.6 Band Lineup at Semiconductor Heterostructures:
       Tight-Binding Approach ........................................ 98
   6.7 Historical Notes ............................................... 100

7. Cleaved {110} Surfaces of III-V
   and II-VI Compound Semiconductors ....................... 105
   7.1 Ionicity and Core-Level Spectroscopy
       of Compound Semiconductors ................................. 105
   7.1.1 Layer Model of Photoemitted Electrons ..................... 105
   7.1.2 Charge Transfer in the Bulk
       of Compound Semiconductors .................................. 109
   7.2 Surface Core-Level Shifts .................................. 112
   7.3 Geometrical Surface Structure ................................ 114
   7.4 Surface Phonons ............................................. 122
   7.5 Electronic Surface States .................................. 128
   7.5.1 Intrinsic Versus Extrinsic Surface States ................... 128
   7.5.2 Cleavage-Induced Surface States:
       InAs(110) as an Example ..................................... 131
   7.5.3 Intrinsic Surface States ................................... 133
   7.6 Temperature Dependence of the Ionization Energy .......... 137
   7.7 Chemical Trends of the Ionization Energy ................... 140

8. {100} Surfaces of III-V, II-VI,
   and I-VII Compound Semiconductors
   with Zincblende Structure .................................. 145
   8.1 Reconstructions and Trends in Chemical Compositions ...... 145
   8.2 Dimerization ............................................... 150
   8.3 Missing Dimer Structures .................................... 153
   8.4 Dimerization, Occupation of Dangling Bonds,
       and Electron Counting ....................................... 161
   8.5 Intrinsic Surface Band Structure ............................ 166
   8.6 Fermi-Level Pinning by Extrinsic Surface States ............. 167
   8.7 Ionization Energy .......................................... 168

9. {100} Surfaces of Diamond, Silicon, Germanium,
   and Cubic Silicon Carbide .................................. 169
   9.1 Atomic Arrangement ........................................... 169
9.2 Strain Effects on Si(001) Surfaces ........................................... 175
9.3 Electronic Surface Properties .............................................. 177
9.4 Surface Core-Level Shifts ................................................. 181
9.5 Reversible $2 \times 1 \rightleftharpoons c(4 \times 2)$ Surface Phase Transition ........ 183
9.6 $\beta$-SiC(001) Surfaces .................................................. 186

10. Diamond, Silicon, and Germanium
\{111\}-2 $\times$ 1 Surfaces .................................................. 193
10.1 Cleaved Silicon and Germanium Surfaces ............................. 194
  10.1.1 Early Models of (111)-2 $\times$ 1 Reconstructions
  and Core-Level Shifts .................................................. 194
  10.1.2 Band Structure of Dangling-Bond Surface States:
  Experimental Data ...................................................... 197
  10.1.3 Surface Band Gap .................................................. 202
  10.1.4 Tilted Chains ................................................... 206
  10.1.5 Band Structure of Dangling-Bond Surface States:
  Theoretical Results ................................................... 213
10.2 Clean Diamond \{111\} Surfaces ........................................ 213
  10.2.1 Atomic Arrangement ............................................. 213
  10.2.2 Electronic Properties .......................................... 215
10.3 Clean Diamond and Cleaved Silicon
  and Germanium \{111\} Surfaces in Comparison ...................... 217

11. Si(111)-7 $\times$ 7 and Ge(111)-c(2 $\times$ 8) Surfaces ........... 219
11.1 Preparation of Clean Si(111)-7 $\times$ 7
  and Ge(111)-c(2 $\times$ 8) Surfaces .................................. 219
11.2 Si(111)-7 $\times$ 7: Atomic Arrangement .......................... 221
  11.2.1 Elements of the 7 $\times$ 7 Reconstruction
  on Si(111) Surfaces .................................................. 221
  11.2.2 Dimer-Adatom-Stacking Fault Model ......................... 225
11.3 Ge(111)-c(2 $\times$ 8): Atomic Arrangement ....................... 229
11.4 Electronic Structure of Si(111)-7 $\times$ 7
  and Ge(111)-c(2 $\times$ 8) Surfaces .................................. 232
  11.4.1 Electronic Band Structure ................................... 232
  11.4.2 Core-Level Spectroscopy .................................... 234
11.5 Energetics of Reconstructions on \{111\} Surfaces
  of Si and Ge: 7 $\times$ 7 Versus c(2 $\times$ 8) ...................... 237

12. Phase Transitions on Silicon and Germanium
\{111\} Surfaces ........................................................ 241
12.1 Si(111)-7 $\times$ 7 $\Rightarrow$ “1 $\times$ 1”
  and Ge(111)-c(2 $\times$ 8) $\Rightarrow$ “1 $\times$ 1” Phase Transitions ........ 241
12.2 Ge(111)-“1 $\times$ 1” High-Temperature Phase Transition ......... 246
12.3 Irreversible Conversion of 2 $\times$ 1 Reconstructions
  on Cleaved Si and Ge Surfaces ...................................... 247
13. \{111\} Surfaces of Compounds with Zincblende Structure . 255
13.1 [111]-Oriented Surfaces ........................................... 255
13.2 [\overline{111}]-Oriented Surfaces ................................. 257

14. Monovalent Adatoms ............................................. 263
14.1 Adsorption of Halogens ......................................... 263
14.1.1 Dissociative Adsorption ...................................... 263
14.1.2 Bond Lengths and Adsorption Sites ...................... 269
14.2 Adsorption of Hydrogen ......................................... 272
14.2.1 Si(001):H-Surfaces ........................................ 272
14.2.2 Si(111):H-\(\delta(7 \times 7)\) Surfaces ...................... 275
14.2.3 Si(111)- and Ge(111):H-1 \times 1 Surfaces ............ 276
14.3 Alkali and Silver Adatoms on Si\{100\} Surfaces ......... 280
14.4 Monovalent Metal Adatoms on Si and Ge \{111\} Surfaces .. 283
14.4.1 Alkali Adatoms on Si\{111\}-7 \times 7 Surfaces ......... 283
14.4.2 Si(111):Ag- and Ge(111):Ag-(\(\sqrt{3} \times \sqrt{3}\))R30° Structures ........................................ 284
14.4.3 Si(111):Au- and Ge(111):Au-(\(\sqrt{3} \times \sqrt{3}\))R30° Structures ........................................ 287
14.4.4 \(3 \times 1\) Reconstructions Induced by Alkali and Silver Adatoms on Si \{111\} Surfaces .......... 288
14.5 Growth Kinetics of Metals on Cleaved GaAs\{110\} Surfaces ... 291
14.6 Adatom-Induced Surface Core-Level Shifts .............. 300
14.7 Adatom-Induced Surface Dipoles ............................ 307
14.7.1 Mutual Interactions in Plane Arrays of Surface Dipoles ........................................ 307
14.7.2 Surface Dipoles Induced by Alkali Adatoms .......... 309
14.7.3 Hydrogen-Induced Surface Dipoles ...................... 311
14.8 Adatom-Induced Surface States ............................... 316
14.8.1 Cesium Adatoms on Cleaved Si Surfaces ............... 316
14.8.2 Metal Adatoms on GaAs\{110\} Surfaces ............... 317
14.8.3 Nonmetal Adatoms on GaAs\{110\} Surfaces .......... 324

15. Group-III Adatoms on Silicon Surfaces ...................... 329
15.1 Si\{111\}:\text{III-(}\sqrt{3} \times \sqrt{3})\text{R}30°\) Reconstructions ........................................ 329
15.1.1 Al-, Ga-, and In-Induced \((\sqrt{3} \times \sqrt{3})\text{R}30°\) Reconstructions ........................................ 330
15.1.2 B-Induced \((\sqrt{3} \times \sqrt{3})\text{R}30°\) Reconstruction ........................................ 333
15.2 Reconstructions Induced by Group-III Adatoms on \{100\} Surfaces of Si and Ge ............. 334

16.1 Si\{111\}:\text{As-}1 \times 1 and Si\{001\}:As- and Si\{001\}:Sb-2 \times 1 Surfaces ........................................ 339
Contents XV

16.2 Sb- and Bi-induced (√3 × √3)R30° Structures on Si and Ge(111) Surfaces ................................. 343
16.3 GaP-, GaAs-, and InP(110):Sb-1 × 1 Surfaces ......................... 347
16.4 III-V(110):Bi-1 × 1 Surfaces ........................................ 350

17. Oxidation of Silicon and III-V Compound Semiconductors ........................................... 353
17.1 Si(111) Surfaces ........................................ 353
  17.1.1 Precursor-Mediated Chemisorption on Si(111)-7 × 7 Surfaces ................................. 354
  17.1.2 Oxygen-Induced Si(2p) Core-Level Shifts ...................................... 361
  17.1.3 Field-Assisted Oxidation ........................................ 364
17.2 III-V Compound Semiconductors ........................................ 366
  17.2.1 Oxidation Kinetics on GaAs(110) Surfaces ............................ 367
  17.2.2 Photon-Stimulated Oxidation ........................................ 371
  17.2.3 Core-Level Spectroscopy: Growth Mode and Composition of Oxide Films .... 372

18. Surface Passivation by Adsorbates and Surfactants .......... 377
18.1 Surface Passivation by Hydrogen ...................................... 377
18.2 Surfactant-Mediated Growth ........................................ 381

19. Semiconductor Interfaces ........................................ 385
19.1 Metal–Semiconductor Contacts ...................................... 386
  19.1.1 Current Transport Across Metal–Semiconductor Contacts .......... 386
  19.1.2 Image-Force Effect ........................................ 388
  19.1.3 Determination of Barrier Heights: A Brief Comparison of Methods ............ 389
  19.1.4 Barrier Heights of Real Schottky Contacts .................................. 392
  19.1.5 Laterally Inhomogeneous Schottky Contacts 1: Circular Patches .............. 400
  19.1.6 Laterally Inhomogeneous Schottky Contacts 2: BEEM .......................... 402
  19.1.7 Laterally Inhomogeneous Schottky Contacts 3: I/V Characteristics .......... 402
  19.1.8 The MIGS-and-Electron negativity Concept: Experiment and Theory .......... 407
  19.1.9 Direct Observations of MIGS ...................................... 418
  19.1.10 Extrinsic Interface Dipoles 1: Interface Doping ....................... 420
  19.1.11 Extrinsic Interface Dipoles 2: Metal/Si(111)-(7 × 7)i Contacts ............. 424
  19.1.12 Extrinsic Interface Dipoles 3: Epitaxial Silicide/Silicon Interfaces ........ 427
XVI  Contents

19.1.13 Origin of Lateral Barrier-Height Inhomogeneities 1:
   Natural Nonuniformities ..........................  434
19.1.14 Origin of Lateral Barrier-Height Inhomogeneities 2:
   Extrinsic Nonuniformities ........................  435
19.1.15 Slope Parameter  ................................  437
19.1.16 Schottky Contacts on Ternary III-V Alloys ..........  439
19.1.17 Temperature and High-Pressure Effects ..........  444
19.1.18 Ohmic Contacts ..................................  451
19.2 Semiconductor Heterostructures ..........................  455
   19.2.1 Band-Structure Lineup ...........................  455
   19.2.2 Interface Dipoles at Polar Interfaces ...............  457
   19.2.3 Lattice-Matched Ternary and Quaternary III-V Alloys .....................................  461
   19.2.4 Pressure and Temperature Dependence
       of Valence-Band Offsets .........................  467
   19.2.5 Pseudomorphic Interfaces ........................  468
   19.2.6 Metamorphic Heterostructures ....................  471
19.3 Layered Semiconductors ..................................  472
19.4 Insulator Interfaces .....................................  476
   19.4.1 Metal–Insulator Contacts ..........................  476
   19.4.2 Semiconductor–Insulator Interfaces ...............  479

Appendix ................................................  483

References ................................................  487

Index of Reconstructions and Adsorbates .....................  535

Subject Index .............................................  539
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